

L Number	Hits	Search Text	DB	Time stamp
1	31363	semiconductor and sample and stage	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:15
2	7813	(semiconductor and sample and stage) and defect	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:15
3	640	((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:16
4	347	((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:17
5	95	(((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:17
6	95	(((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:18
7	73	(((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image) and irradiation	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:18
8	59	((((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image) and irradiation) and resolution	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:19
9	56	((((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image) and irradiation) and resolution) and (emitted or emission)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:20
10	1	((((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image) and irradiation) and resolution) and (emitted or emission)) and (first adj resolution)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:21
11	53	((((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image) and irradiation) and resolution) and (emitted or emission)) and magnification	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:22
12	23	((((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image) and irradiation) and resolution) and (emitted or emission)) and magnification) and (magnification adj image)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:43
13	1	((((((semiconductor and sample and stage) and defect) and (secondary adj (electron or particle)))) and target) and (position near4 defect)) and image) and irradiation) and resolution) and (emitted or emission)) and magnification) and (magnification adj image)) and (plural adj defects)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/28 11:39